



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-03D Plastic-Encapsulate DIODE

DK70LLD03

SWITCHING DIODE

DESCRIPTION

Epitaxial planar Silicon diode

FEATURES

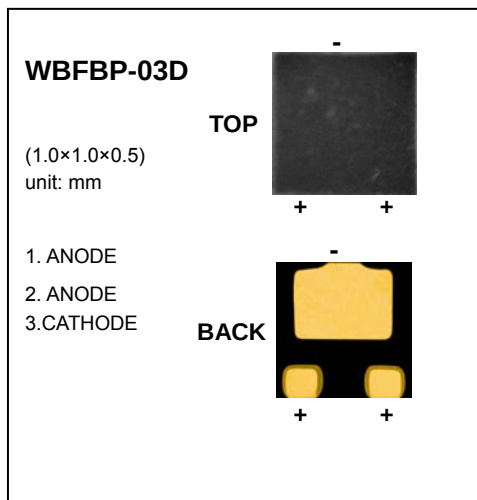
Fast Switching Speed

Ultra-Small Surface Mount Package

For General Purpose Switching Applications

High Conductance

Lead Free Product

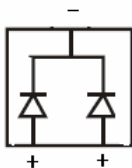
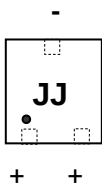


APPLICATION

For General Purpose Switching Applications, rectifiers

For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC,etc.)

MARKING: JJ



Maximum Ratings @T_A=25°C

Parameter	Symbol	Limits	Unit
Reverse voltage	V_R	85	V
Forward current	I_o	75	mA
Forward power dissipation	P_D	100	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65~150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu A$	85		V
Reverse voltage leakage current	I_{R1}	$V_R = 75V$		2	μA
	I_{R2}	$V_R = 25V$		0.03	μA
Forward voltage	V_F	$I_F = 1mA,$ $I_F = 10mA,$ $I_F = 50mA$ $I_F = 150mA$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R = 0, f = 1MHz$		1.5	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10mA, I_{rr} = 0.1 \times I_R, R_L = 100\Omega$		4	nS

